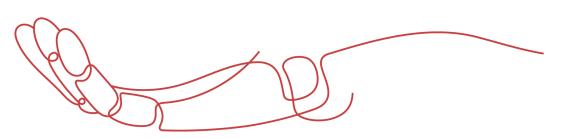




PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

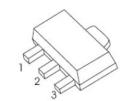
urces Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

TRANSISTOR(NPN)

FEATURES

Power dissipation



1. BASE

2. COLLECTOR

SOT-89-3L

3. EMITTER

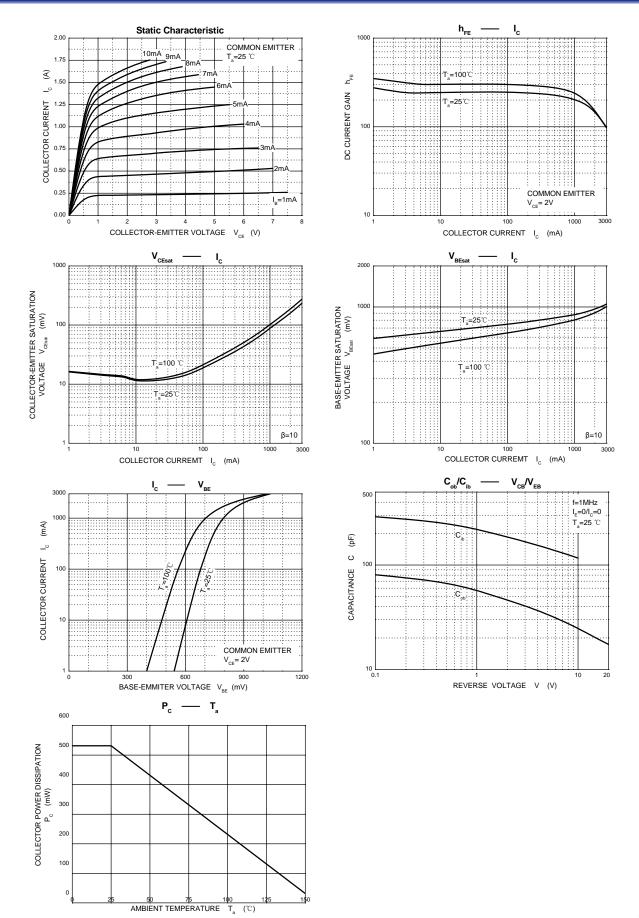
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	40	V	
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{EBO}	Emitter-Base Voltage	6	V	
Ic	Collector Current -Continuous	3	А	
Pc	Collector Power Dissipation	0.5	W	
R _{OJA}	Thermal Resistance from AAA Junction to Ambient	Á25€	°C/W	
R _{eJC}	Thermal Resistance from ÁÁÁ Junction to Case	Á35	°C/W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~150	°C	

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

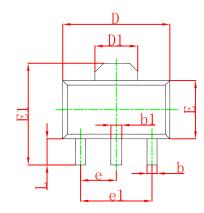
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	$I_C = 100 \mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	$I_C = 10 \text{mA}, I_B = 0$	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μΑ, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} = 40V, I _E =0			1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 30V, I _B =0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 6V, I _C =0			1	μA
DC ourrent goin	h _{FE(1)}	V _{CE} =2V, I _C = 1A	60		400	
DC current gain	h _{FE(2)}	V _{CE} =2V, I _C = 100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 2A, I _B = 0.2 A			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 2A, I _B = 0.2 A			1.5	V
Transition frequency	f _T	V _{CE} = 5V , Ic=0.1A f =10MHz	50			MHz

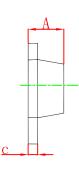






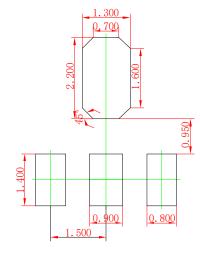
SOT-89-3L Package Outline Dimensions





Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550 REF.		0.061 REF.		
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000 TYP.		0.118 TYP.		
Ĺ	0.900	1.200	0.035	0.047	

SOT-89-3L Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.



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